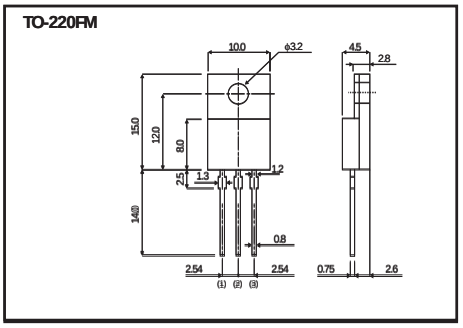
10V Drive Nch MOSFET

ZDX130N50

● Structure
Silicon N-channel MOSFET

● Dimensions (Unit : mm)



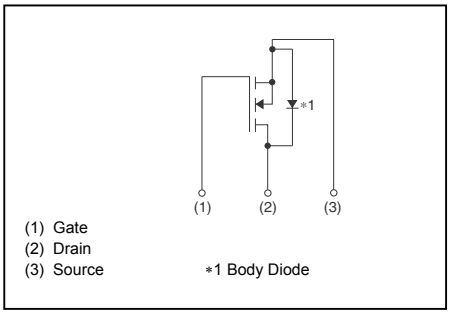
●Features
1) Low on-resistance.
2) High-speed switching.
3) Gate-source voltage
   V_{GSS} guaranteed to be ±30V .
4) High package power.

● Application
Switching

● Packaging specifications

Type	Package	Bulk
	Code	-
	Basic ordering unit (pieces)	500
ZDX130N50		○

● Inner circuit



● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	500	V
Gate-source voltage		V_{GSS}	±30	V
Drain current	Continuous	I_D	±13	A
	Pulsed	I_{DP} *1	±39	A
Source current (Body Diode)	Continuous	I_S	13	A
	Pulsed	I_{SP} *1	39	A
Avalanche current		I_{AS} *3	10	A
Avalanche energy		E_{AS} *3	50	mJ
Power dissipation		P_D *2	40	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%

*2 Tc=25°C

*3 L≒1mH, V_{DD}=50V, R_G=25Ω Starting Tch=25°C

● Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Case	Rth (ch-c)	3.125	°C / W

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● **Electrical characteristics** (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	±100	nA	V_{GS}=±30V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)DSS}$	500	-	-	V	I_D=1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	-	-	100	μA	V_{DS}=500V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	2.5	-	4.5	V	V_{DS}=10V, I_D=1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$*	-	0.4	0.52	Ω	I_D=6.5A, V_{GS}=10V
Forward transfer admittance	$\|Y_{fs}\|$*	2.0	8.5	-	S	V_{DS}=10V, I_D=6.0A
Input capacitance	C_{iss}	-	2180	-	pF	V_{DS}=25V
Output capacitance	C_{oss}	-	200	-	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	-	60	-	pF	f=1MHz
Turn-on delay time	$t_{d(on)}$*	-	30	-	ns	V_{DD}≒250V, I_D=5.0A
Rise time	t_r *	-	25	-	ns	V_{GS}=10V
Turn-off delay time	$t_{d(off)}$*	-	43	-	ns	R_L=50Ω, R_G=10Ω
Fall time	t_f *	-	15	-	ns	
Total gate charge	Q_g *	-	40	-	nC	V_{DD}≒250V, I_D=5.0A
Gate-source charge	Q_{gs} *	-	11.5	-	nC	V_{GS}=10V
Gate-drain charge	Q_{gd} *	-	12.5	-	nC	

*Pulsed

●**Body diode characteristics** (Source-Drain)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD} *	-	-	1.7	V	I_s=13A, V_{GS}=0V

*Pulsed

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●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics (Ⅰ)

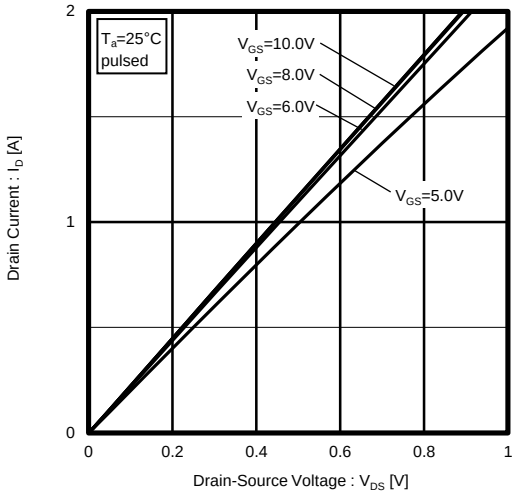


Fig.2 Typical Output Characteristics(Ⅱ)

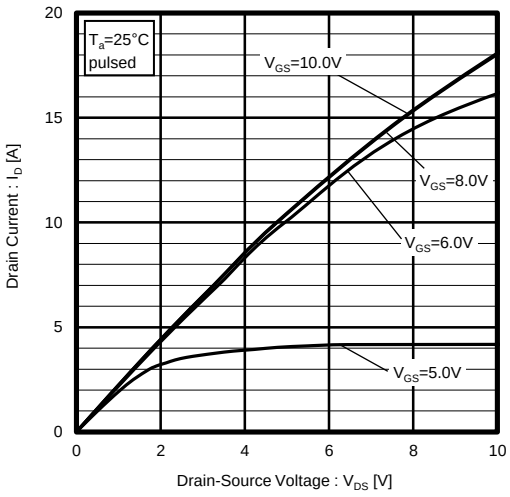


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

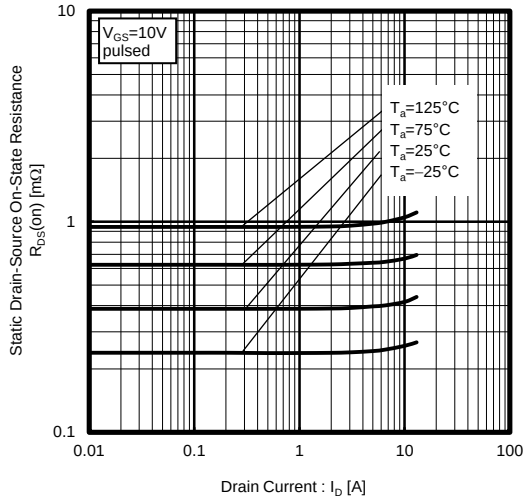


Fig.4 Forward Transfer Admittance vs. Drain Current

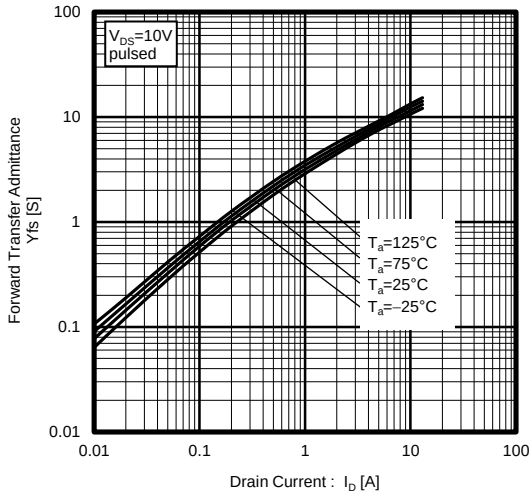


Fig.5 Typical Transfer Characteristics

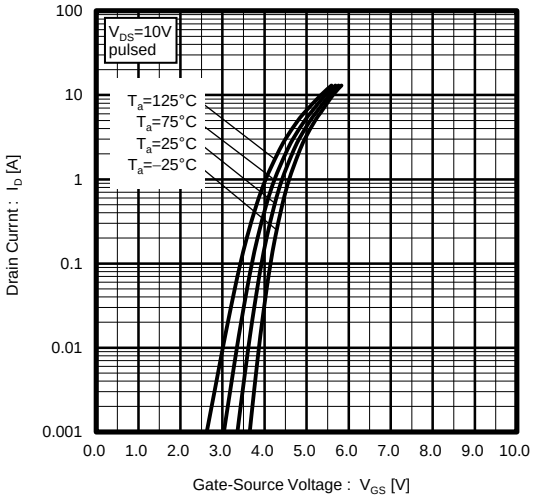
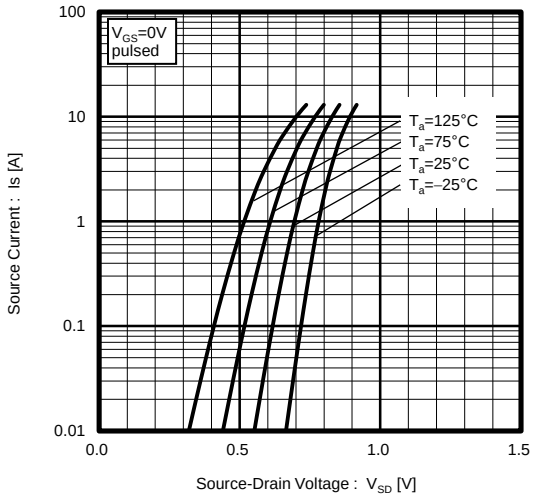


Fig.6 Source Current vs. Source-Drain Voltage



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Fig.7 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

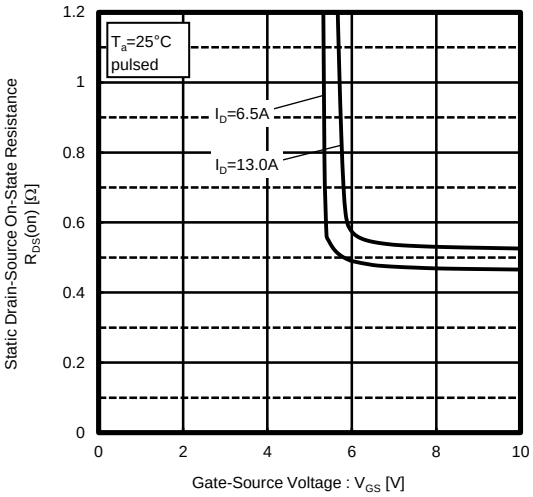


Fig.8 Switching Characteristics

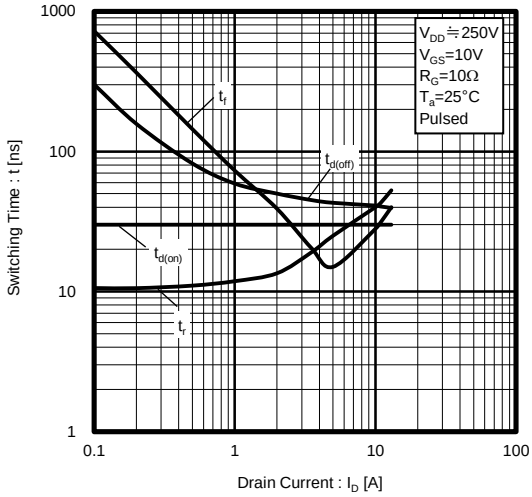


Fig.9 Dynamic Input Characteristics

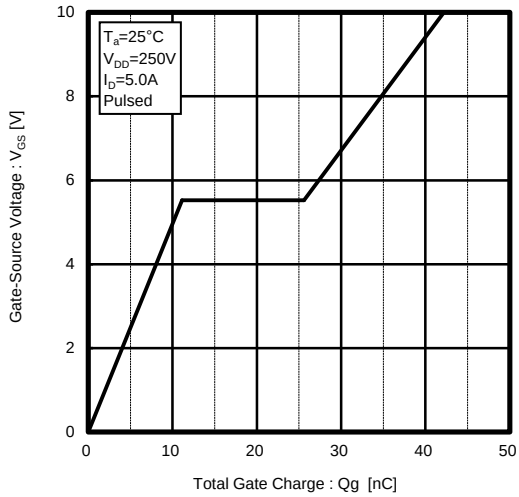


Fig.10 Typical Capacitance vs. Drain-Source Voltage

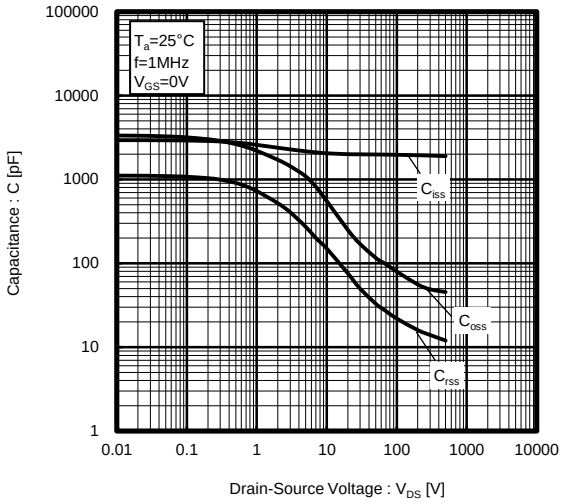
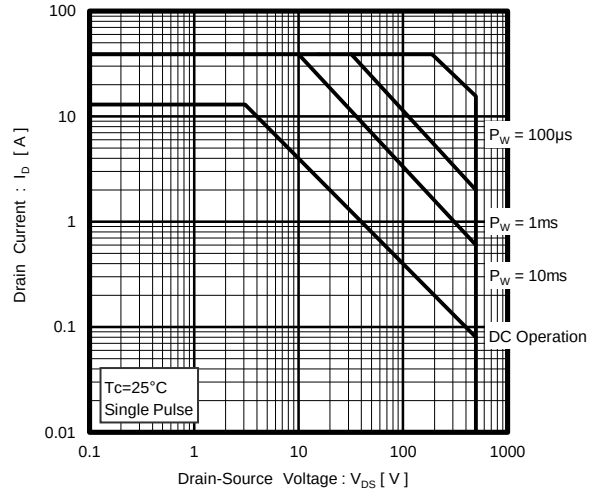


Fig.11 Maximum Safe Operating Area



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● Measurement circuits

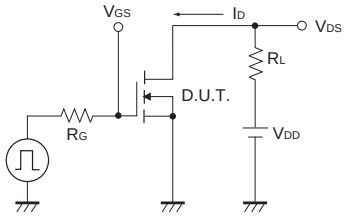


Fig.1-1 Switching Time Measurement Circuit

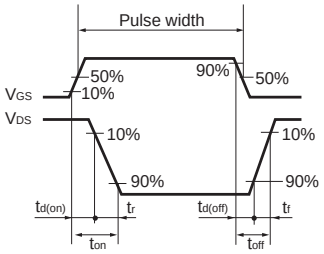


Fig.1-2 Switching Waveforms

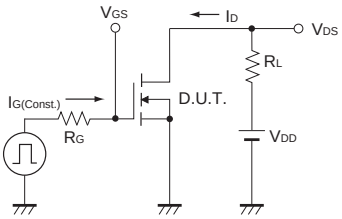


Fig.2-1 Gate Charge Measurement Circuit

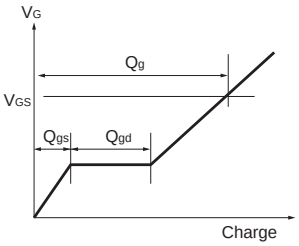


Fig.2-2 Gate Charge Waveform

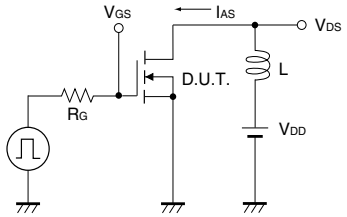


Fig.3-1 Avalanche Measurement Circuit

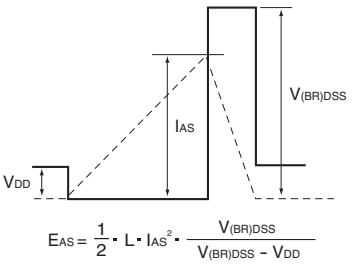


Fig.3-2 Avalanche Waveform

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